

# Darlington Complementary Silicon Power Transistors

## MJH6284 (NPN), MJH6287 (PNP)

These devices are designed for general-purpose amplifier and low-speed switching motor control applications.

### Features

- Similar to the Popular NPN 2N6284 and the PNP 2N6287
- Rugged RBSOA Characteristics
- Monolithic Construction with Built-in Collector-Emitter Diode
- These are Pb-Free Devices\*

### MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	Vdc
Collector-Base Voltage	$V_{CB}$	100	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current – Continuous – Peak	$I_C$	20 40	Adc
Base Current	$I_B$	0.5	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	160 1.28	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.78	$^\circ\text{C/W}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

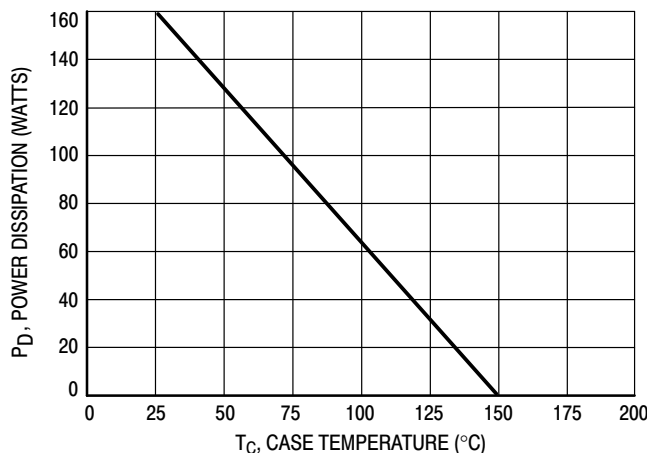
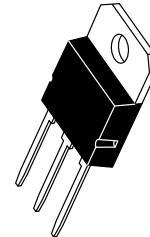


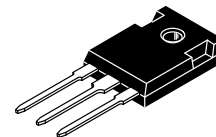
Figure 1. Power Derating

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## DARLINGTON 20 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 100 VOLTS, 160 WATTS



SOT-93  
(TO-218)  
CASE 340D



TO-247  
CASE 340L  
STYLE 3

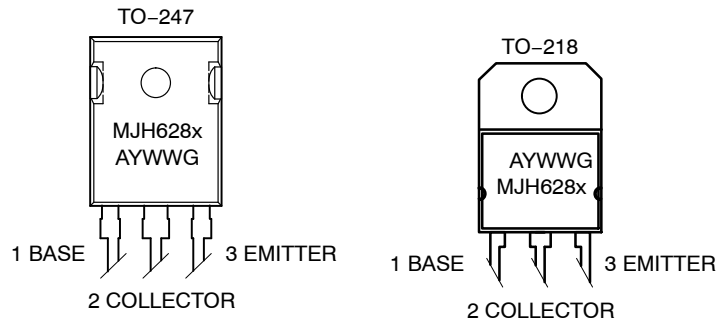
**NOTE:** Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# MJH6284 (NPN), MJH6287 (PNP)

## MARKING DIAGRAMS



MJH628x = Device Code  
x = 4 or 7  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

## ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MJH6284G	TO-218 (Pb-Free)	30 Units / Rail
MJH6287G	TO-218 (Pb-Free)	30 Units / Rail
MJH6284G	TO-247 (Pb-Free)	30 Units / Rail
MJH6287G	TO-247 (Pb-Free)	30 Units / Rail

## MJH6284 (NPN), MJH6287 (PNP)

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage ( $I_C = 0.1 \text{ Adc}$ , $I_B = 0$ )	$V_{CEO(sus)}$	100	–	Vdc
Collector Cutoff Current ( $V_{CE} = 50 \text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	–	1.0	mAdc
Collector Cutoff Current ( $V_{CE} = \text{Rated } V_{CB}$ , $V_{BE(off)} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = \text{Rated } V_{CB}$ , $V_{BE(off)} = 1.5 \text{ Vdc}$ , $T_C = 150^\circ\text{C}$ )	$I_{CEX}$	– –	0.5 5.0	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	2.0	mAdc

### ON CHARACTERISTICS (Note 1)

DC Current Gain ( $I_C = 10 \text{ Adc}$ , $V_{CE} = 3.0 \text{ Vdc}$ ) ( $I_C = 20 \text{ Adc}$ , $V_{CE} = 3.0 \text{ Vdc}$ )	$h_{FE}$	750 100	18,000 –	–
Collector–Emitter Saturation Voltage ( $I_C = 10 \text{ Adc}$ , $I_B = 40 \text{ mAdc}$ ) ( $I_C = 20 \text{ Adc}$ , $I_B = 200 \text{ mAdc}$ )	$V_{CE(sat)}$	– –	2.0 3.0	Vdc
Base–Emitter On Voltage ( $I_C = 10 \text{ Adc}$ , $V_{CE} = 3.0 \text{ Vdc}$ )	$V_{BE(on)}$	–	2.8	Vdc
Base–Emitter Saturation Voltage ( $I_C = 20 \text{ Adc}$ , $I_B = 200 \text{ mAdc}$ )	$V_{BE(sat)}$	–	4.0	Vdc

## DYNAMIC CHARACTERISTICS

Current–Gain Bandwidth Product ( $I_C = 10\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$f_T$	4.0	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 0.1\text{ MHz}$ )  MJD6284 MJD6287	$C_{ob}$	– –	400 600	pF
Small–Signal Current Gain ( $I_C = 10\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	300	–	–

## SWITCHING CHARACTERISTICS

Resistive Load		Symbol	Typical		Unit
			NPN	PNP	
Delay Time	$V_{CC} = 30 \text{ Vdc}$ , $I_C = 10 \text{ Adc}$ $I_{B1} = I_{B2} = 100 \text{ mA}$ Duty Cycle = 1.0%	$t_d$	0.1	0.1	$\mu\text{s}$
Rise Time		$t_r$	0.3	0.3	
Storage Time		$t_s$	1.0	1.0	
Fall Time		$t_f$	3.5	2.0	

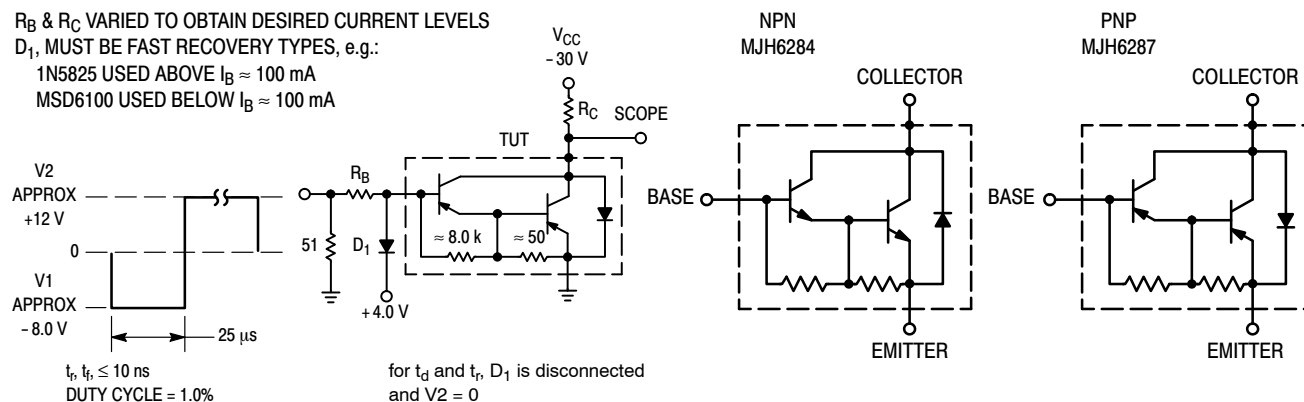
1. Pulse test: Pulse Width = 300  $\mu$ s, Duty Cycle = 2.0%.

### R<sub>B</sub> & R<sub>C</sub> VARIED TO OBTAIN DESIRED CURRENT LEVELS

D<sub>1</sub>, MUST BE FAST RECOVERY TYPES, e.g.:

1N5825 USED ABOVE  $I_B \approx 100$  mA

MSD6100 USED BELOW  $I_B \approx 100$  mA



For NPN test circuit reverse diode and voltage polarities.

### Figure 2. Switching Times Test Circuit

### Figure 3. Darlington Schematic

## MJH6284 (NPN), MJH6287 (PNP)

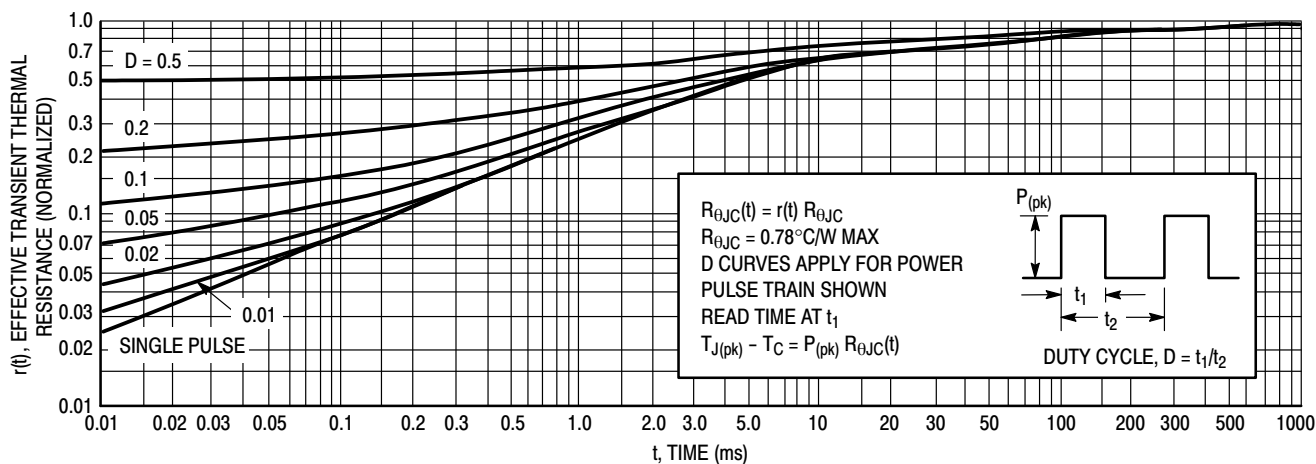


Figure 4. Thermal Response

### FBSOA, FORWARD BIAS SAFE OPERATING AREA

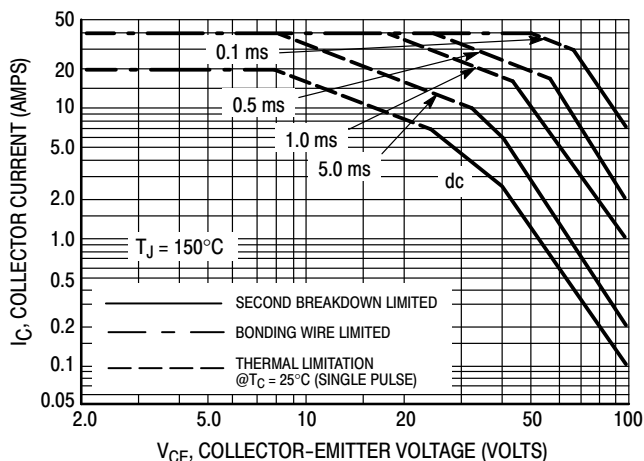


Figure 5. MJH6284, MJH6287

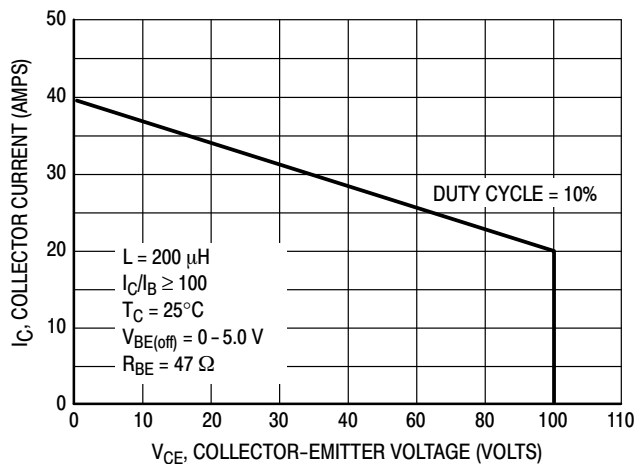


Figure 6. Maximum RBSOA, Reverse Bias Safe Operating Area

### FORWARD BIAS

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# MJH6284 (NPN), MJH6287 (PNP)

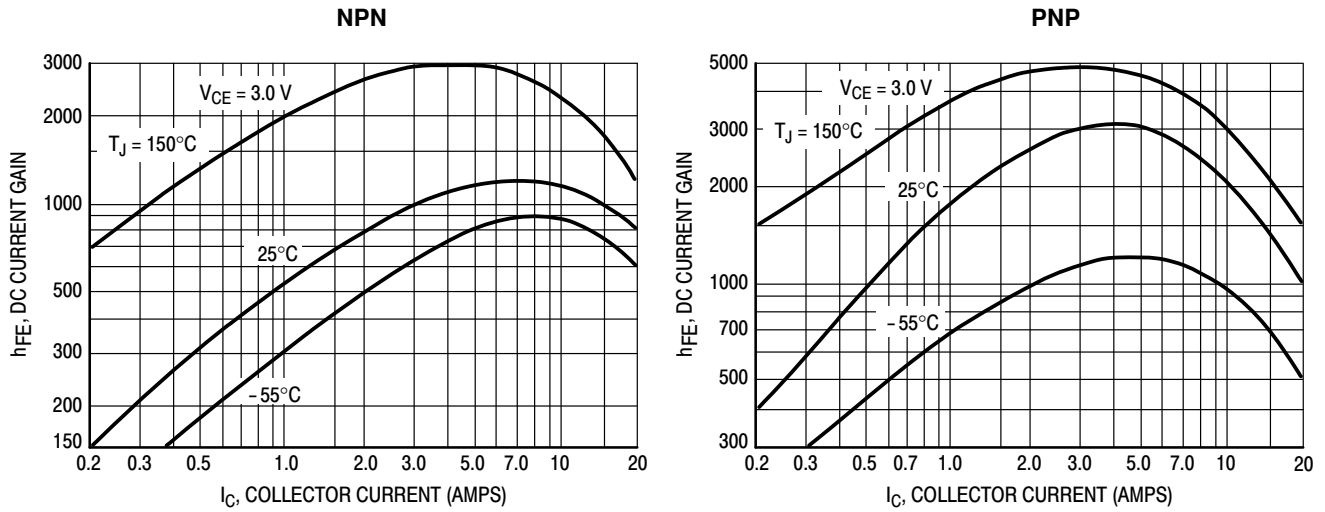


Figure 7. DC Current Gain

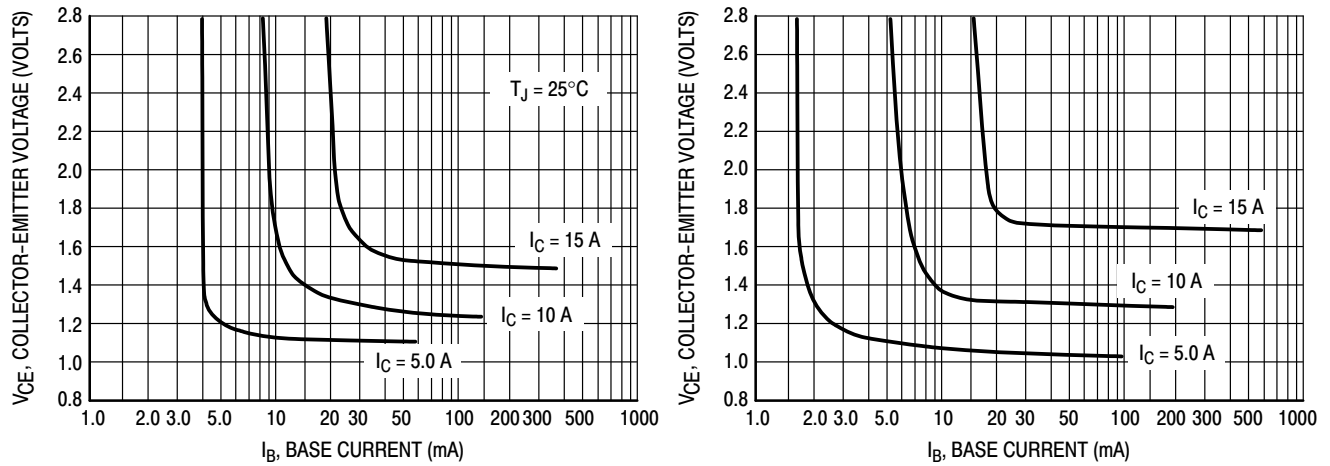


Figure 8. Collector Saturation Region

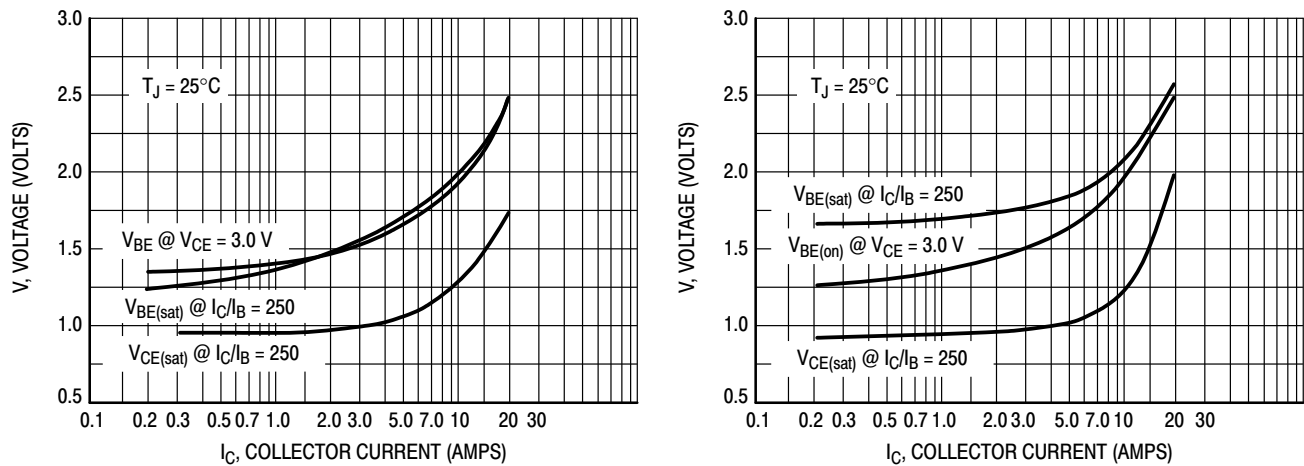
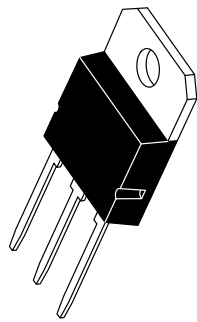
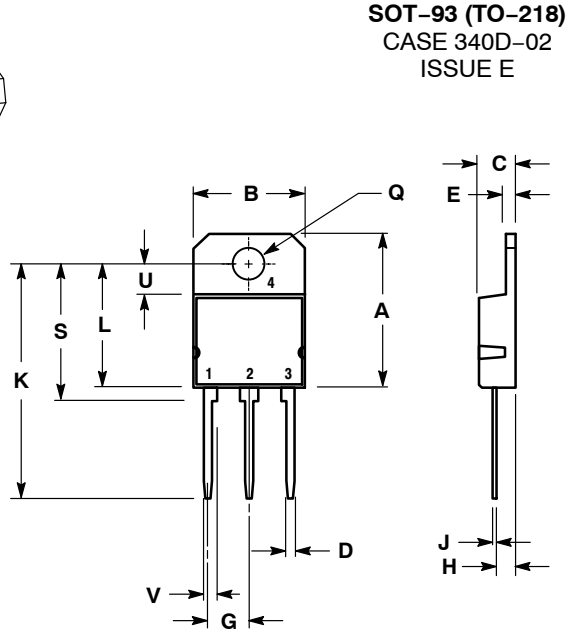


Figure 9. "On" Voltages



SCALE 1:1



STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

SOT-93 (TO-218)  
CASE 340D-02  
ISSUE E

DATE 03 JAN 2002

- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

GENERIC  
MARKING DIAGRAM\*

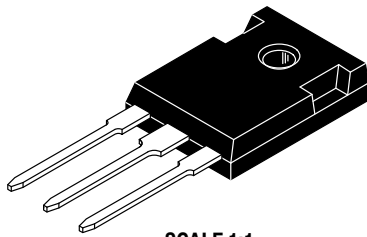


A = Assembly Location  
Y = Year  
WW = Work Week  
XXXXX = Device Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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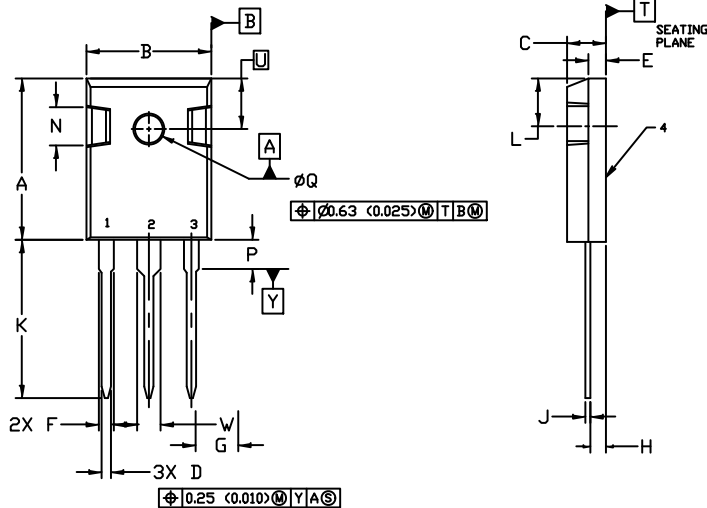
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TO-247  
CASE 340L  
ISSUE G

DATE 06 OCT 2021

SCALE 1:1

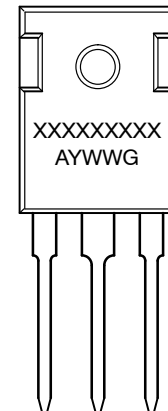


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER

	MILLIMETERS		INCHES	
DIM	MIN.	MAX.	MIN.	MAX.
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	----	4.50	----	0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

GENERIC  
MARKING DIAGRAM\*



STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 2: PIN 1. ANODE 2. CATHODE (S) 3. ANODE 2 4. CATHODE (S)	STYLE 3: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 4: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR
STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE	STYLE 6: PIN 1. MAIN TERMINAL 1 2. MAIN TERMINAL 2 3. GATE 4. MAIN TERMINAL 2		

XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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